INTEGRATED CIRCUITS



Product data Supersedes data of 1998 Apr 20 2003 Mar 10



Philips Semiconductors

Triple 3-input NOR gate

FEATURES

- Wide operating voltage: 1.0 to 5.5 V
- Optimized for Low Voltage applications: 1.0 to 3.6 V
- \bullet Accepts TTL input levels between V_{CC} = 2.7 V and V_{CC} = 3.6 V
- Typical V_{OLP} (output ground bounce) < 0.8 V at V_{CC} = 3.3 V, T_{amb} = 25 °C.
- Typical V_{OHV} (output V_{OH} undershoot) > 2 V at V_{CC} = 3.3 V, T_{amb} = 25 °C.
- Output capability: standard
- I_{CC} category: SSI

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25 \text{ °C}$; $t_r = t_f \le 2.5 \text{ ns}$

DESCRIPTION

The 74LV27 is a low-voltage Si-gate CMOS device and is pin and function compatible with 74HC/HCT27.

The 74LV27 provides the 3-input NOR function.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t _{PHL} /t _{PLH}	Propagation delay nA, nB, nC to nY	C _L = 15 pF; V _{CC} = 3.3 V 8		ns
C _I Input capacitance			3.5	pF
C _{PD}	Power dissipation capacitance per gate	See Notes 1 and 2	24	pF

NOTES:

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μ W) $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where: N = number of outputs switching; $\begin{array}{l} f_i = \text{input frequency in MHz; } C_L = \text{output load capacitance in pF;} \\ f_o = \text{output frequency in MHz; } V_{CC} = \text{supply voltage in V;} \\ \Sigma \left(C_L \times V_{CC}^2 \times f_o \right) = \text{sum of the outputs.} \end{array}$ $\begin{array}{l} \text{2. The condition is } V_I = \text{GND to } V_{CC}. \end{array}$

ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	ORDER CODE	PKG. DWG. #
14-Pin Plastic SO	–40 °C to +125 °C	74LV27D	SOT108-1

PIN CONFIGURATION



PIN DESCRIPTION

PIN NUMBER SYMBOL		NAME AND FUNCTION
1, 3, 9	1A – 3A	Data inputs
2, 4, 10	1B – 3B	Data inputs
13, 5, 11	1C – 3C	Data inputs
7	GND	Ground (0 V)
12, 6, 8	1Y – 3Y	Data outputs
14	V _{CC}	Positive supply voltage

Triple 3-input NOR gate

74LV27

LOGIC SYMBOL



LOGIC DIAGRAM



RECOMMENDED OPERATING CONDITIONS

SYMBOL CONDITIONS UNIT PARAMETER MIN TYP MAX See Note 1 5.5 DC supply voltage 1.0 3.3 V V_{CC} V VI Input voltage 0 _ V_{CC} V_{O} Output voltage 0 _ V_{CC} V See DC and AC -40 +85 °C Operating ambient temperature range in free air Tamb characteristics -40 +125 V_{CC} = 1.0 V to 2.0 V 500 ns/V _ _ $V_{CC} = 2.0 \text{ V to } 2.7 \text{ V}$ 200 ns/V _ _ Input rise and fall times t_r, t_f V_{CC} = 2.7 V to 3.6 V _ _ 100 ns/V V_{CC} = 3.6 V to 5.5 V 50 ns/V _ _

NOTE:

1. The LV is guaranteed to function down to V_{CC} = 1.0 V (input levels GND or V_{CC}); DC characteristics are guaranteed from V_{CC} = 1.2 V to V_{CC} = 5.5 V.

LOGIC SYMBOL (IEEE/IEC)



FUNCTION TABLE

	OUTPUTS		
nA	nB	nC	nY
L	L	L	Н
X	Х	н	L
X	н	Х	L
н	Х	Х	L

NOTES:

H = HIGH voltage level L = LOW voltage level X = don't care

ABSOLUTE MAXIMUM RATINGS^{1, 2}

In accordance with the Absolute Maximum Rating System (IEC 134). Voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +7.0	V
±I _{IK}	DC input diode current	$V_{\rm I} < -0.5$ V or $V_{\rm I} > V_{\rm CC} + 0.5$ V	20	mA
±І _{ОК}	DC output diode current	V_{O} < -0.5 V or V_{O} > V_{CC} + 0.5 V	50	mA
±ΙΟ	DC output source or sink current (standard outputs)	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	25	mA
±I _{GND} , ±I _{CC}	DC V_{CC} or GND current for types with standard outputs		50	mA
T _{stg}	Storage temperature range		-65 to +150	°C
P _{TOT}	Power dissipation per package – plastic mini-pack (SO)	for temperature range: -40 to +125 °C above +70 °C derate linearly with 8 mW/K	500	mW

NOTES:

 Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

2. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

DC ELECTRICAL CHARACTERISTICS

Over recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

			LIMITS						
SYMBOL	PARAMETER	TEST CONDITIONS	–40 °C to +85 °C			–40 °C to +125 °C		TINU	
			MIN	TYP ¹	MAX	MIN	MAX	1	
		V _{CC} = 1.2 V	0.9			0.9			
V	HIGH level Input	V _{CC} = 2.0 V	1.4			1.4			
V_{IH}	voltage	V _{CC} = 2.7 V to 3.6 V	2.0			2.0		1 `	
		V _{CC} = 4.5 V to 5.5 V	0.7 * V _{CC}			0.7 * V _{CC}		1	
		V _{CC} = 1.2 V			0.3		0.3		
M.	LOW level Input	V _{CC} = 2.0 V			0.6		0.6		
VIL	voltage	V _{CC} = 2.7 V to 3.6 V			0.8		0.8	1 `	
		V _{CC} = 4.5 V to 5.5 V			0.3 * V _{CC}		0.3 * V _{CC}	1	
		$V_{CC} = 1.2 \text{ V}; \text{ V}_{I} = V_{IH} \text{ or } \text{V}_{IL;} - \text{I}_{O} = 100 \mu\text{A}$		1.2					
		$V_{CC} = 2.0 \text{ V}; \text{ V}_{I} = V_{IH} \text{ or } \text{V}_{IL;} - \text{I}_{O} = 100 \mu\text{A}$	1.8	2.0		1.8		V	
V _{OH}	HIGH level output voltage; all outputs	V_{CC} = 2.7 V; V_I = V_{IH} or V_{IL} ; $-I_O$ = 100 μ A	2.5	2.7		2.5			
		$V_{CC} = 3.0 \text{ V}; \text{ V}_{I} = V_{IH} \text{ or } \text{V}_{IL;} - \text{I}_{O} = 100 \mu\text{A}$	2.8	3.0		2.8			
		V_{CC} = 4.5 V; V_{I} = V_{IH} or V_{IL} ; $-I_{O}$ = 100 μ A	4.3	4.5		4.3			
V _{OH}	HIGH level output voltage; STANDARD outputs	V_{CC} = 3.0 V; V_{I} = V_{IH} or $V_{IL;}$ –I_O = 6 mA	2.40	2.82		2.20		v	
♥ OH		V_{CC} = 4.5 V; V_I = V_{IH} or $V_{IL;}$ – I_O = 12 mA	3.60	4.20		3.50			
		V_{CC} = 1.2 V; V_I = V_{IH} or V_{IL} ; I_O = 100 μ A		0					
		V_{CC} = 2.0 V; V_I = V_{IH} or V_{IL} ; I_O = 100 μ A		0	0.2		0.2		
V _{OL}	LOW level output voltage; all outputs	V_{CC} = 2.7 V; V_I = V_{IH} or V_{IL} ; I_O = 100 μ A		0	0.2		0.2		
	······	V_{CC} = 3.0 V; V_{I} = V_{IH} or $V_{IL;}$ I_{O} = 100 μA		0	0.2		0.2	1	
		V_{CC} = 4.5 V; V_{I} = V_{IH} or $V_{IL;}$ I_{O} = 100 μA		0	0.2		0.2		
Ve	LOW level output voltage; STANDARD	V_{CC} = 3.0 V; V_{I} = V_{IH} or $V_{IL;}$ I_{O} = 6 mA		0.25	0.40		0.50	v	
	outputs	V_{CC} = 4.5 V; V_I = V_{IH} or $V_{IL;}$ I_O = 12 mA		0.35	0.55		0.65	ľ	
I	Input leakage current	V_{CC} = 5.5 V; V_{I} = V_{CC} or GND			1.0		1.0	μΑ	
I _{CC}	Quiescent supply current; SSI	$V_{CC} = 5.5 \text{ V}; \text{ V}_{I} = V_{CC} \text{ or GND}; \text{ I}_{O} = 0$			20.0		40	μΑ	
ΔI_{CC}	Additional quiescent supply current	V_{CC} = 2.7 V to 3.6 V; V_{I} = V_{CC} – 0.6 V			500		850	μΑ	

NOTE:

1. All typical values are measured at T_{amb} = 25 $^\circ C.$

AC CHARACTERISTICS

GND = 0 V; $t_r = t_f \le 2.5$ ns; $C_L = 50$ pF; $R_L = 1$ k Ω

			CONDITION			LIMITS			
SYMBOL	PARAMETER	WAVEFORM	CONDITION	-40) °C to +85	°C	–40 °C to	• +125 °C	UNIT
			V _{CC} (V)	MIN	TYP ¹	MAX	MIN	MAX	
		1.2		50					
			2.0		17	22		27	
t _{PHL/PLH}	t _{PHL/PLH} Propagation delay nA, nB, nC to nY	Figures 1, 2	2.7		13	16		20	ns
		3.0 to 3.6		10 ²	13		16		
			4.5 to 5.5			11		14	

NOTES:

1. Unless otherwise stated, all typical values are measured at $T_{amb} = 25 \text{ °C}$ 2. Typical values are measured at $V_{CC} = 3.3 \text{ V}$.

AC WAVEFORMS

 V_M = 1.5 V at $V_{CC} \geq 2.7$ V and ≤ 3.6 V; V_M = 0.5 \times V_{CC} at V_{CC} < 2.7 V and \geq 4.5 V; $V_{\mbox{OL}}$ and $V_{\mbox{OH}}$ are the typical output voltage drop that occur with the output load.



Figure 1. Input (nA, nB, nC) to output (nY) propagation delays.

TEST CIRCUIT



Figure 2. Load circuitry for switching times.

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74LV27



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Product data

74LV27

REVISION HISTORY

Rev	Date	Description
_4	20030310	Product data (9397 750 11225). ECN 853-1896 29488 of 07 February 2003. Supersedes Product specification of 1998 Apr 20 (9397 750 04412).
		Modifications:
		• Delete DIL, SSOP and TSSOP package ordering and package outlines (discontinued options).
		Quick Reference Data: Correct power dissipation formula in Note 1.
_3	19980420	Product specification (9397 750 04412). ECN 853-1896 19258 of 20 April 1998. Supersedes data of 1997 Feb 03.

Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2] [3]}	Definitions			
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.			
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.			
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[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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Date of release: 03-03

9397 750 11225

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